

• General Description

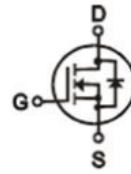
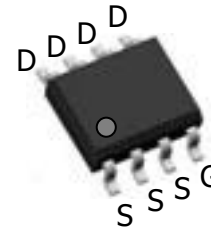
The ZM065N06S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification in DC/DC and AC/DC Converters
- Industrial and Motor Drive applications
- POL application

• Product Summary

 $V_{DS}=60V$
 $R_{DS(ON)} = 5.9m\Omega$
 $I_D=18A$

SOP-8
• Ordering Information:

Part NO.	ZM065N06S
Marking	ZM065N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	18	A
	$I_D @ T_C = 75^\circ C$	13.7	A
	$I_D @ T_C = 100^\circ C$	11.3	A
Pulsed Drain Current ①	I_{DM}	55	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	80	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	2.5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy @ $L=0.1mH$	E_{AS}	150	mJ
Avalanche Current @ $L=0.1mH$	I_{AS}	60	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	1.6	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =16A		5.9	7	mΩ
		V _{GS} =4.5V, I _D =10A		7.5	9	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =8A		28		s
Source-drain voltage	V _{SD}	I _S =16A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =20V f = 1MHz	-	4100	-	pF
Output capacitance	C _{oss}		-	226	-	
Reverse transfer capacitance	C _{rss}		-	144	-	

•Switching Parameters(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 25V	-	58	-	nC
Gate - Source charge	Q _{gs}	I _D = 15A	-	14.8	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	6.9	-	
Body Diode Reverse Recovery Time	t _{rr}	I _F =20A, di/dt=100A/μs		27		nS
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =20A, di/dt=100A/μs		65		nC

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Fig.1 Gate-Charge Characteristics

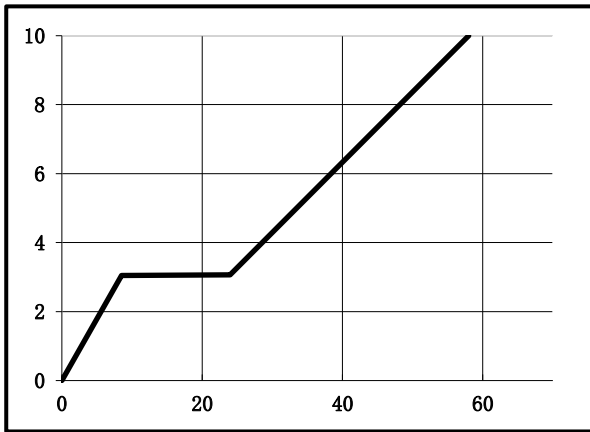


Fig.2 Capacitance Characteristics

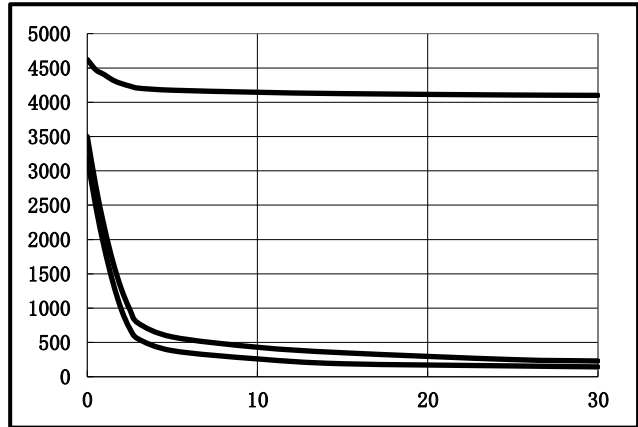


Fig.3 Power Dissipation

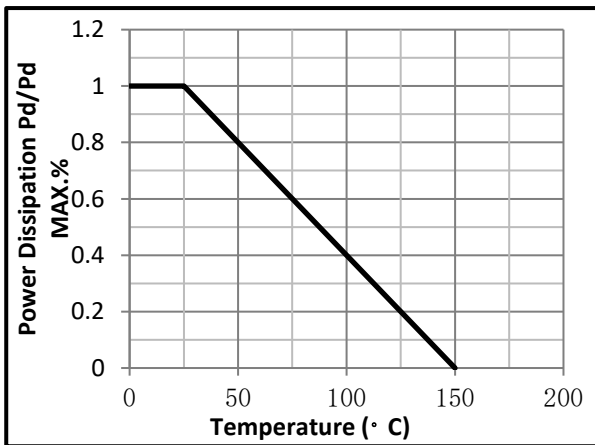


Fig.4 Typical output Characteristics

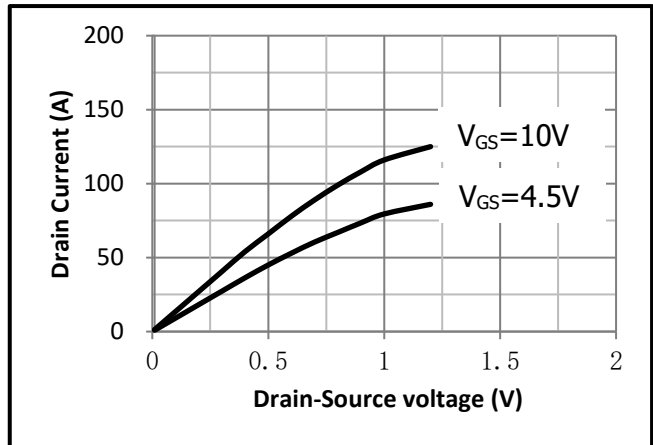


Fig.5 Threshold Voltage V.S Junction Temperature

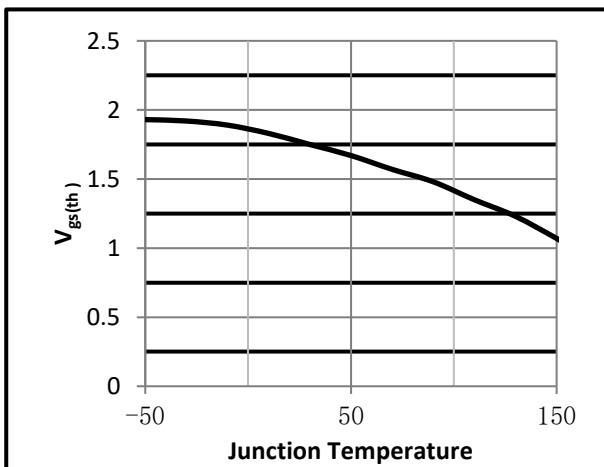


Fig.6 Resistance V.S Drain Current

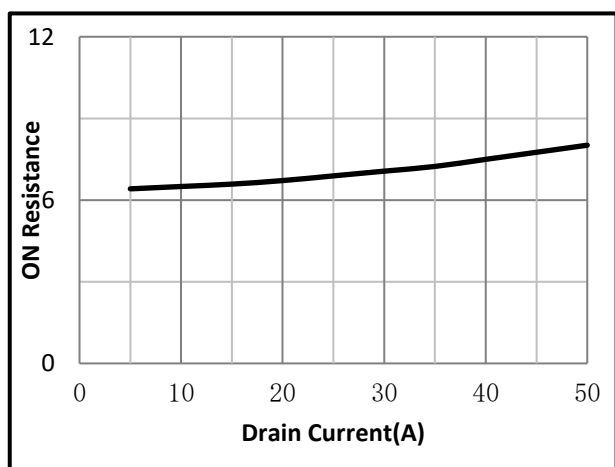


Fig.7 On-Resistance VS Gate Source Voltage

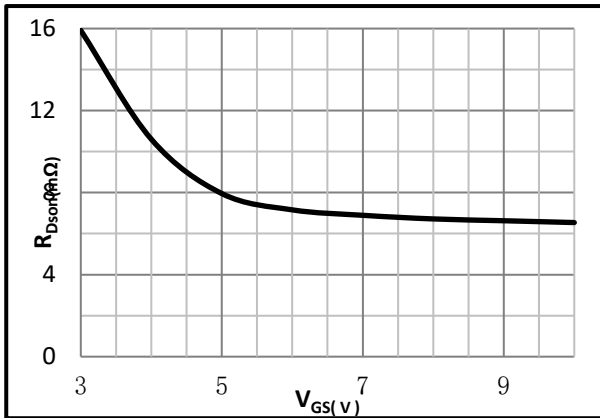


Fig.8 On-Resistance V.S Junction Temperature

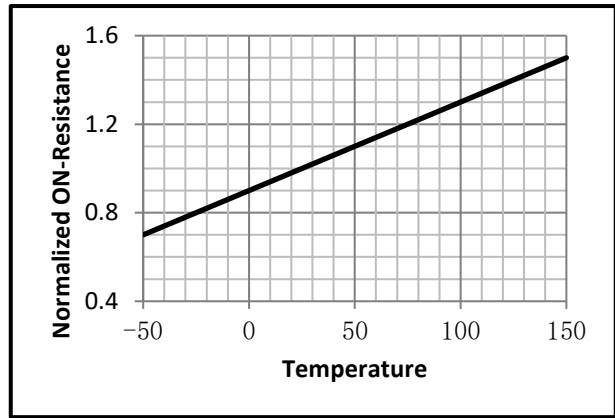


Fig.9 Switching Time Measurement Circuit

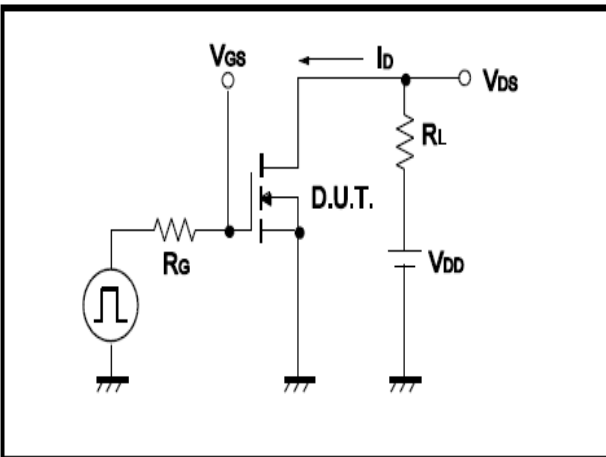


Fig.10 Gate Charge Waveform

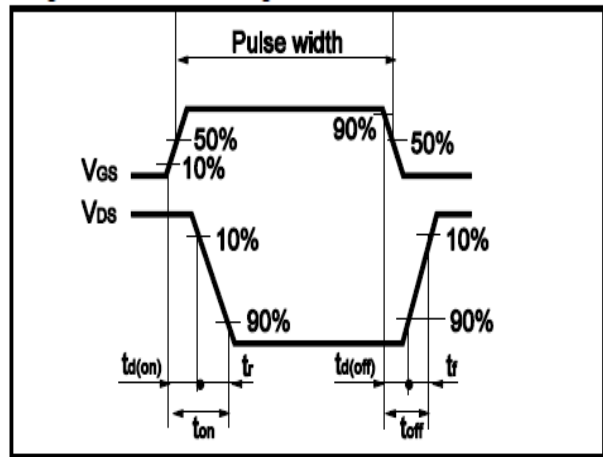


Fig.11 Avalanche Measurement Circuit

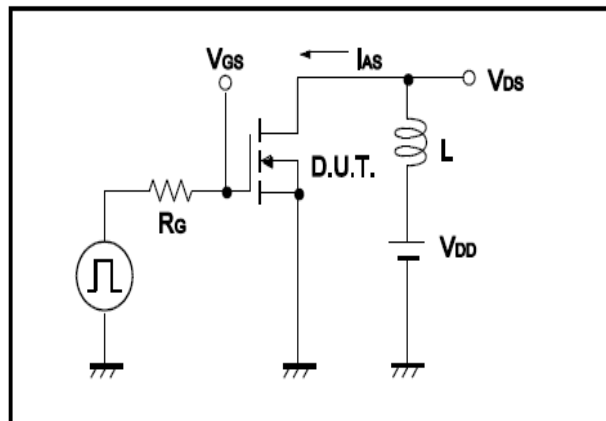
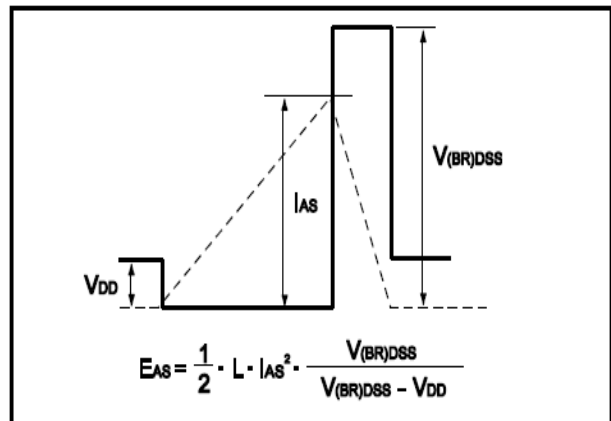


Fig.12 Avalanche Waveform



●Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

